

Impacts of growth temperature on electrical properties of Mg-doped AlGa_N films grown by RF-MBE under nitrogen-rich conditions

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Deep ultraviolet (DUV) light is widely used in the medical and sterilization fields. Especially, emission wavelengths shorter than 220 nm is recently recognized as human-friendly sterilization light [1,2]. AlGa_N alloys are promising material for the DUV emitters. But, one of the drawbacks is monotonic increase in an activation energy of Mg acceptor [3,4]. In this study, Mg-doped Al_xGa_{1-x}N films were grown by the RF-MBE under nitrogen-rich conditions.

407-848-nm-thick Mg-doped Al_xGa_{1-x}N films were grown on 425-nm-thick c-plane AlN on Al₂O₃ templates [5] for 1 hour. The beam equivalent pressures (BEP) of Al and Ga were respectively set as 3.0×10^{-8} and 2.7×10^{-7} Torr, with a nitrogen flow rate of 1.0 ccm and RF Power of 150 W. Mg was supplied from effusion cell with temperature of 360°C. Thermocouple substrate temperature (T_{sub}) was varied from 675 to 750°C. Mg-doped GaN films were also grown at the same T_{sub} range for comparison. The films were evaluated using spectroscopic ellipsometry (SE), atomic force microscopy (AFM), X-ray diffraction (XRD), infrared reflectance, Hall effect, and Seebeck effect measurements.

Values obtained by the Hall effect and Seebeck effect measurements at room temperature (RT) are summarized. It indicates that the Mg-doped AlGa_N film grown at 725°C revealed a hole density of $9.5 \times 10^{18} \text{ cm}^{-3}$.

The results indicate suitable T_{sub} range depends on x for the growth of Mg-doped AlGa_N under the nitrogen-rich condition.

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